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8/7/02 Hayes
PATENT APPLICATION
ATTORNEY DOCKET NO. Q56320

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of

Kaoru NARITA

Appln. No.: 09/421,273

Group Art Unit: 2823

Confirmation No.: 3894

Examiner: J. Garcia

Filed: October 20, 1999

For: SEMICONDUCTOR DEVICE HAVING PROTECTION CIRCUIT IMPLEMENTED BY
BIPOLAR TRANSISTOR FOR DISCHARGING STATIC CHARGE CURRENT AND
PROCESS OF FABRICATION

AMENDMENT UNDER 37 C.F.R. § 1.111

Commissioner for Patents
Washington, D.C. 20231

Sir:

In response to the Office Action dated May 6, 2002, please amend the above identified application as follows:

IN THE CLAIMS:

Please enter the following amended claims:

1. (Twice Amended) A semiconductor device comprising:
- a semiconductor substrate of one conductivity type;
 - shallow trench isolating regions having a first depth, and disposed in surface portions of said semiconductor substrate and defining active areas therebetween;
 - a terminal connected to one of said active areas;
 - a first source of constant voltage connected to another of said active areas;

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